

ABSTRACT OF THE DISCLOSURE

The invention includes methods of forming metal silicide having bulk resistance of less than 30 micro-ohms-centimeter. The metal of the metal silicide can be selected from Groups 3, 4, 8, 9 and 10 of the periodic table, with an exemplary metal being titanium. An exemplary method includes forming a titanium-containing layer directly against tantalum silicide. After the titanium-containing layer is formed directly against the tantalum silicide, titanium of the titanium-containing layer is converted to titanium silicide. Constructions formed in accordance with methodology of the present invention can be incorporated into circuitry associated with semiconductor devices, such as, for example, wordlines and bitlines.